# VS-2EFH01HM3

**Vishay Semiconductors** 

# Hyperfast Rectifier, 2 A FRED Pt®



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Cathode O Anode

## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 A			
V <sub>R</sub>	100 V			
V <sub>F</sub> at I <sub>F</sub> (typ. 125 °C)	0.75 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMF (DO-219AB)			
Circuit configuration	Single			

### FEATURES

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- Compatible to SOD-123W package case outline
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

## **MECHANICAL DATA**

Case: SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V <sub>RRM</sub>		100	V			
Average rectified forward current	I <sub>F(AV)</sub>	$T_{\rm C} = 150 \ ^{\circ}{\rm C} \ ^{(1)}$	2	٨			
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	50	A			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

#### Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

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<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	100	-	-	
Forward voltage	VF	I <sub>F</sub> = 2 A	-	0.88	0.95	V
Forward voltage	۷F	I <sub>F</sub> = 2 A, T <sub>J</sub> = 125 °C	-	0.75	0.82	
Reverse leakage current	I <sub>R</sub> -	V <sub>R</sub> = V <sub>R</sub> rated	-	-	2	
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	0.5	8	μA
Junction capacitance	CT	V <sub>R</sub> = 100 V	-	8	-	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$	õs, V <sub>R</sub> = 30 V	-	24	-	
Reverse recovery time	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr}$	= 0.25 A	-	-	25	ns A
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	16	-	
		T <sub>J</sub> = 125 °C		-	22	-	
Poole recovery ourrent		T <sub>J</sub> = 25 °C	$I_F = 2 A$	-	2	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 160 V	-	3	-	
Davience and a second shares	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	16	-	nC
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	30	-	no

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to mount	R <sub>thJM</sub>	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	15	°C/W	
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	130	°C/W	
Approvimete weight				0.015		g	
Approximate weight				0.0005		oz.	
Marking device		Case style SMF (DO-219AB)		M	BH		



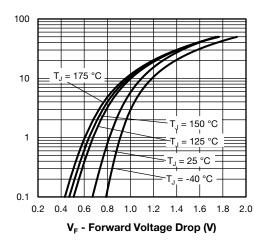


Fig. 1 - Typical Forward Voltage Drop Characteristics

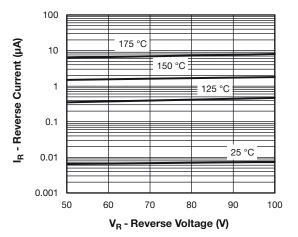


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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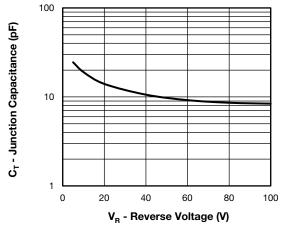
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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

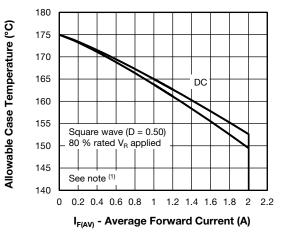


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

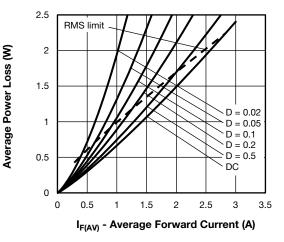


Fig. 5 - Forward Power Loss Characteristics

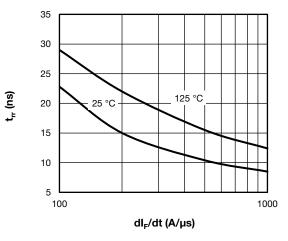
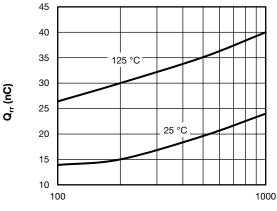


Fig. 6 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt



dl<sub>F</sub>/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ 5); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

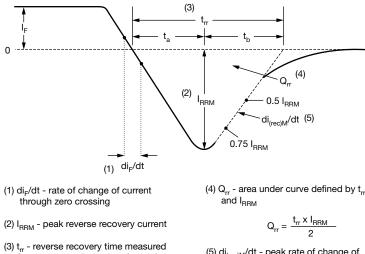
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(3)  $t_{\rm rr}$  - reverse recovery time measured from zero crossing point of negative going  ${\rm I}_{\rm F}$  to point where a line passing through 0.75 I<sub>RBM</sub> and 0.50 I<sub>RBM</sub> extrapolated to zero current.

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

## **ORDERING INFORMATION TABLE**

SHAY

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Device code	vs-	2	Е	F	н	01	н	МЗ
	1	2	3	4	5	6	7	8
	1 · 2 · 3 ·	- Cur - Circ	rent rat cuit con	nicondu ing (2 = figuratio	2 A)	oduct		
	4 - 5 -	- F = - Pro	single o SMF pa cess ty	ackage pe,				
	6 - 7 - 8 -	- Vol - H =	tage co AEC-C	ast recov de (01 = 101 qua gen-free,	100 V) alified	complia	ant, and	termin

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIP						
VS-2EFH01HM3/I	10 000	10 000	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95572			
Part marking information	www.vishay.com/doc?95618			
Packaging information	www.vishay.com/doc?95577			
SPICE model	www.vishay.com/doc?96013			

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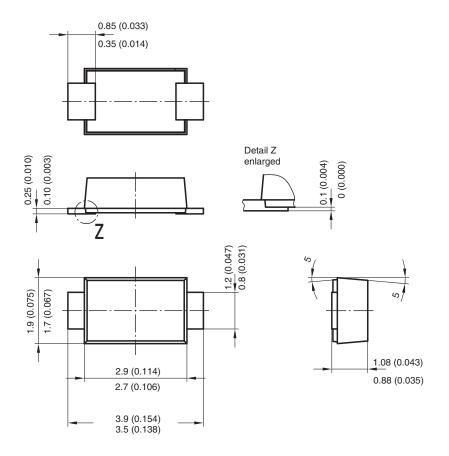
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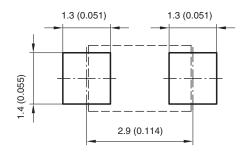
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# SMF (DO-219AB)

### **DIMENSIONS** in millimeters (inches)



Foot print recommendation:



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